

ABSTRACT OF THE DISCLOSURE

The objective of the present invention is to improve drain withstanding voltage at operation.

A semiconductor device of the present invention has a
5 gate electrode 9 formed on a P type semiconductor substrate
1 via gate oxide films 7A and 8, a first low concentration
(LN type) drain region 5 being adjacent to one end of the gate
electrode 9, a second low concentration (SLN type) drain region
6 which is formed a in the first low concentration drain region
10 5 so that said second low concentration drain region 6 is very
close to the outer boundary of said second low concentration
drain region 5 and is at least higher in impurity concentration
than that of the first low concentration drain region 5, a
high concentration (N+ type) source region 10 formed adjacent
15 to the other end of said gate electrode 9, and a high concentration
(N+ type) drain region 11 formed in said second low concentration
drain region 10 having the designated space from one end of
said gate electrode 9.